

Cheng-Han Wu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Top-Gate Staggered a-IGZO TFTs Adopting the Bilayer Gate Insulator for Driving AMOLED. IEEE Transactions on Electron Devices, 2012, 59, 1701-1708.	3.0	24
2	Pö1: Amorphous In ₂ O ₃ ࣘGa ₂ O ₃ ࣘZnO Thin Film Transistors and Integrated Circuits on Flexible and Colorless Polyimide Substrates. Digest of Technical Papers SID International Symposium, 2008, 39, 1207-1210.	0.3	19
3	Comparison of High-Speed PAM4 and QAM-OFDM Data Transmission Using Single-Mode VCSEL in OM5 and OM4 MMF Links. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-10.	2.9	19
4	Comparison on OM5-MMF and OM4-MMF Data Links With 32-GBaud PAM-4 Modulated Few-Mode VCSEL at 850ßnm. Journal of Lightwave Technology, 2020, 38, 573-582.	4.6	7
5	850-nm Single-Mode Vertical-Cavity Surface-Emitting Lasers for 40 Gb/s Error-Free Transmission up to 500 m in OM4 Fiber. IEEE Electron Device Letters, 2020, 41, 84-86.	3.9	7
6	VCSEL with bi-layer oxidized aperture enables 140-Gbit/s OFDM Transmission over 100-m-long OM5 MMF. , 2019, , .		7
7	Self-aligned top-gate amorphous In-Ga-Zn-O thin film transistors. , 2008, , .		1
8	61.4: High-Performance and Highly Rollable a-IGZO TFTs Adopting Composite Electrodes and Transparent Polyimide Substrates. Digest of Technical Papers SID International Symposium, 2010, 41, 921.	0.3	1
9	Pö34: Influences of Channel Deposition Conditions on Characteristics of BottomࣘGate Oxide TFTs Adopting InࣘFree ZincࣘIn Oxides. Digest of Technical Papers SID International Symposium, 2010, 41, 1347-1349.	0.3	0